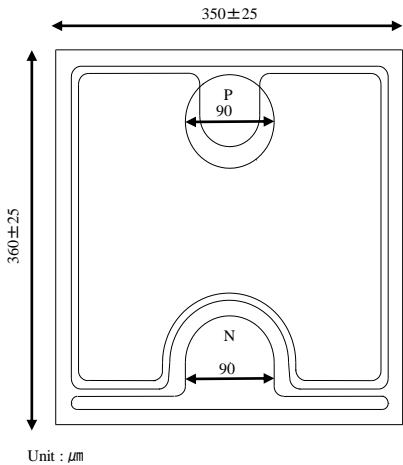


(1) Chip Description

●Mechanical Specification

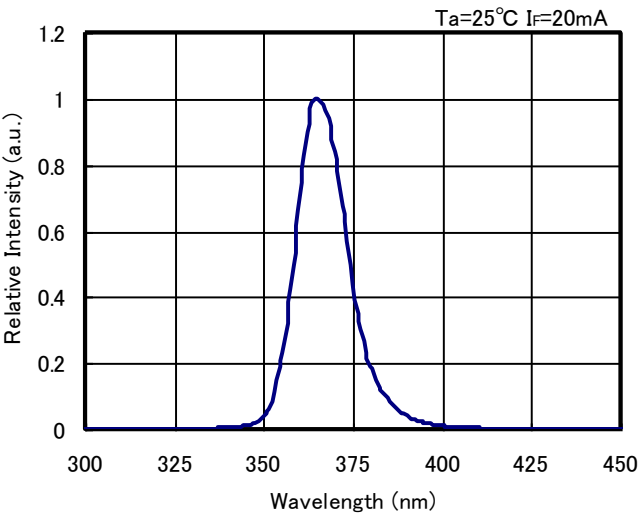
Description	Dimension
Bottom Area	350μm x360μm ± 25μm
Chip Thickness	120μm ± 20μm
N Bonding Pad Electrode	90μm ±5μm
P Bonding Pad Electrode	90μm ±5μm



● Material

- Substrate : Sapphire
- Epitaxial Layer : GaN Based Material
- N Bonding Pad Electrode : Au alloy
- P Bonding Pad Electrode : Au alloy

(2) Spectrum



(3) Optical and Electrical Characteristics (Ta=25°C)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F=20mA$	3.2	3.6	4.2	V
Reverse Current	I_R	$V_R=5V$	-	-	10	μA
Peak Wavelength ^{*1}	λ_p	$I_F=20mA$	365	-	370	nm
Full Width at Half Maximum	$\Delta\lambda$	$I_F=20mA$	10	-	20	nm
Optical Output Power ^{*2}	P_o	$I_F=20mA$	3.5	-	5.0	mW

*1 Measurement error is ±2nm *2 Measurement error is ±10%



CAUTION

- LEDs emit very strong UV radiation.
- Don't look directly into the LED light. UV radiation can harm your eyes.
- To prevent even inadequate exposure, wear protective eyewear.
- If LEDs are embedded in devices, please indicate warning labels against the UV light LED used.
- Keep out of reach of children.
- UV LED chips are very sensitive to static and surge. Take a full protection from static.

Specification and dimension are subject to change for improvement without notice.